VS-10TTS08PbF, VS-10TTS08-M3

Vishay Semiconductors

High Voltage Phase Control Thyristor, 10 A



TO-220AB

PRODUCT SUMMARY			
Package	TO-220AB		
Diode variation	Single SCR		
I _{T(AV)}	6.5 A		
V _{DRM} /V _{RRM}	800 V		
V _{TM}	1.15 V		
I _{GT}	15 mA		
TJ	- 40 °C to 125 °C		

FEATURES

- Designed and qualified according to JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>
 HA

APPLICATIONS

• Typical usage is in input rectification crwobar (soft star) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-10TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS				
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS	
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А	

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	6.5	۸		
I _{T(RMS)}		10	A		
V _{RRM} /V _{DRM}		800	V		
I _{TSM}		140	A		
V _T	6.5 A, T _J = 25 °C	1.15	V		
dV/dt		150	V/µs		
dl/dt		100	A/µs		
TJ	Range	- 40 to 125	°C		

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 ℃ mA
VS-10TTS08PbF, VS-10TTS08-M3	800	800	1.0

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Available



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T 110 °C 100° condu	ation half aine wave	6.5	
Maximum RMS on-state current	I _{T(RMS)}	T _C = 112 °C, 180° conduc	cuon nali sine wave	10	А
Maximum peak, one-cycle,		10 ms sine pulse, rated V	_{RRM} applied, T _J = 125 °C	120	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volta	age reapplied, T _J = 125 °C	140	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V	_{RRM} applied, T _J = 125 °C	72	A2-
ő	1-1	10 ms sine pulse, no voltage reapplied, $T_J = 125 \text{ °C}$		100	A ² s
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C		1000	A²√s
Maximum on-state voltage drop	V _{TM}	6.5 A, T _J = 25 °C		1.15	V
On-state slope resistance	r _t	T 405.00		17.3	mΩ
Threshold voltage	V _{T(TO)}	− T _J = 125 °C		0.85	V
Maximum reverse and direct leakage	1 /1	T _J = 25 °C		0.05	
current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM} / V_{DRM}$	1.0	
Typical holding current	I _H	Anode supply = 6 V, resistive load, initial $I_T = 1 A$		30	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load		50	
Maximum rate of rise of off-state voltage	dV/dt	T _J = 25 °C		150	V/µs
Maximum rate of rise of turned-on current	dl/dt			100	A∕µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+I _{GM}		1.5	А	
Maximum peak negative gate voltage	-V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -65 \text{ °C}$	20		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	15	mA	
		Anode supply = 6 V, resistive load, T_J = 125 °C	10		
Maria and DO and		Anode supply = 6 V, resistive load, T_J = - 65 °C	1.2		
Maximum required DC gate	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	1	.,	
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	V	
Maximum DC gate voltage not to trigger	V_{GD}	$T = 125 \circ C M$ = Poted value	0.2		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T ₁ = 125 °C	3	μs
Typical turn-off time	t _q	1j=125 0	100	

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
Mounting torque	maximum			12 (10)	(lbf ⋅ in)
Marking device			Case style TO-220AB	10TTS	508

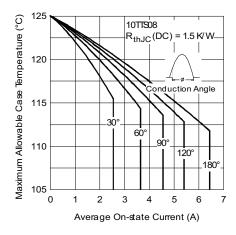


Fig. 1 - Current Rating Characteristics

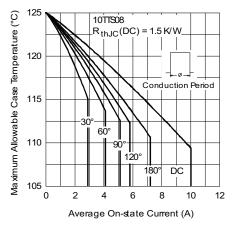


Fig. 2 - Current Rating Characteristic

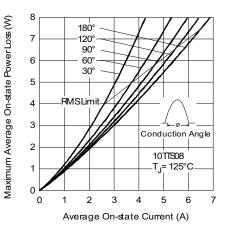


Fig. 3 - On-State Power Loss Characteristics

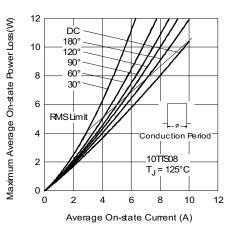


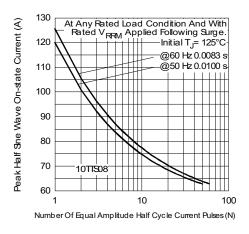
Fig. 4 - On-State Power Loss Characteristics

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Fig. 5 - Maximum Non-Repetitive Surge Current

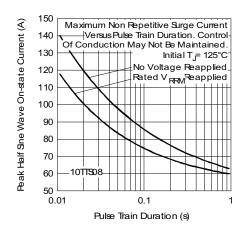


Fig. 6 - Maximum Non-Repetitive Surge Current

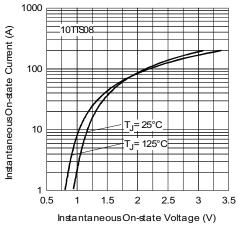


Fig. 7 - On-State Voltage Drop Characteristics

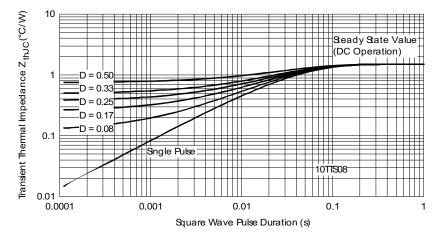


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

De

evice code	VS-	10	т	т	S	08	PbF
		(2)	(3)	(4)	(5)	(6)	(7)
	\bigcirc	(2)	3	4	\bigcirc	\bigcirc	(I)
	1 ·	- Visl	nay Sem	niconduc	ctors pro	duct	
	2 -	- Cur	rent rati	ng			
	3 -	- Circ	cuit con	figuratio	n:		
		T =	Single t	hyristor			
	4	- Pac	kage:				
		T =	TO-220	AB			
	5 -	- Тур	e of sili	con:			
		S =	Conver	ter grad	е		
	6 -	- Vol	tage coo	de x 100	$= V_{RRM}$		
	7 -	- Env	/ironme	ntal digit	:		
		Pbl	= = Lead	l (Pb)-fr	ee and F	RoHS co	omplian
		-M3	3 = Halo	gen-free	e, RoHS	complia	ant, and

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-10TTS08PbF	50	1000	Antistatic plastic tubes			
VS-10TTS08-M3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95222				
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028		



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TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NUTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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